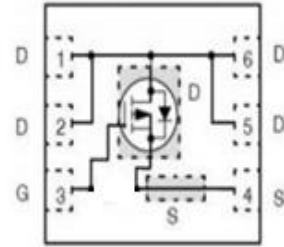
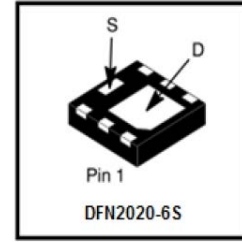


# P3419D

## 30V P-Channel Power MOSFET

### 1. FEATURES

- VDS = -30V  
 $R_{DS(ON)} \leq 30m\Omega, V_{GS@-10V}, I_{DS@-5A}$   
 $R_{DS(ON)} \leq 42m\Omega, V_{GS@-4.5V}, I_{DS@-5A}$
- Low RDS(ON) trench technology.
- Extremely low threshold voltage
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.



### 2. APPLICATIONS

- Portable appliances
- Battery management
- High speed switch

### 3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
P3419D	3B2	4000/Tape&Reel

### 4. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	VDS	-30	V
Gate-Source Voltage	VGS	± 20	
Operating Junction and Storage Temperature Range	TJ , Tstg	-50~+150	°C

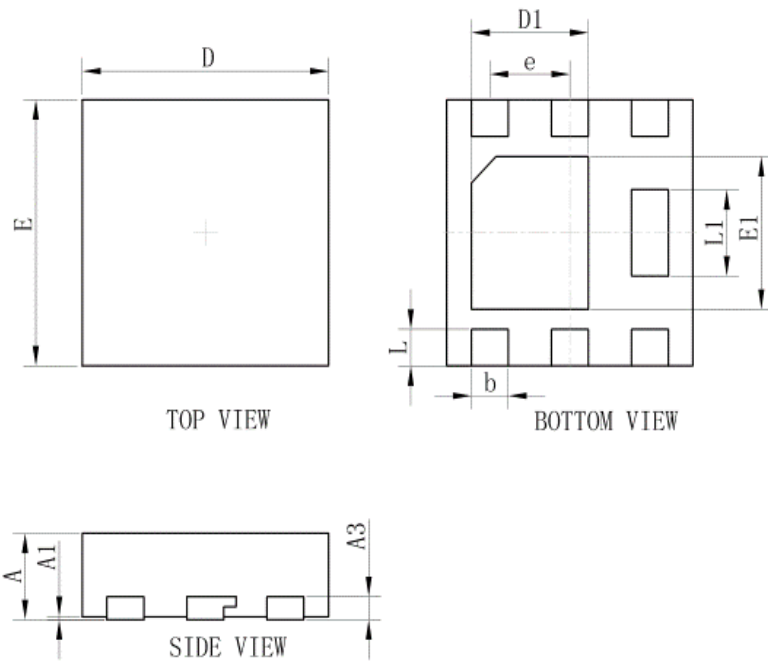


**5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)**

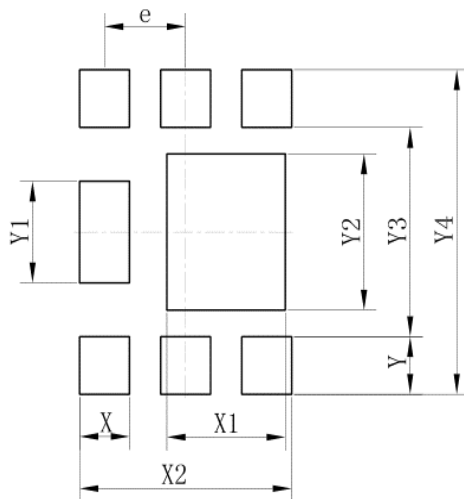
Characteristic	Symbol	Min.	Typ.	Max.	Unit
Static					
Drain-Source Breakdown Voltage (VGS =0V, ID =-250μA)	V(BR)DSS	-30	-	-	V
Gate Threshold Voltage (VDS =VGS , ID =-250μA)	VGS(th)	-0.75	-	-3	V
Gate Leakage Current (VDS =0V, VGS =±20V )	IGSS	-	-	±10	μA
Drain Leakage Current (VDS =-24V, VGS =0V) (VDS =-24V, VGS =0V, TJ = 85 °C)	IDSS	-	-	-1 -30	μA
Drain-Source On-Resistance (VGS =-10V, ID = -5A)	RDS(ON)	-	-	30	mΩ
Drain-Source On-Resistance (VGS =-4.5V, ID = -5A)		-	-	42	
Diode Forward Voltage (IS =-0.5A, VGS =0V)	VSD	-	-	-1.5	V

Note: Pulse test; pulse width ≤ 300us, duty cycle ≤ 2%.



**6. OUTLINE AND DIMENSIONS**


DFN2020-6S			
DIM	MIN	NOR	MAX
A	0.60	0.65	0.70
A1	0.01	0.03	0.05
b	0.25	0.30	0.35
D	1.95	2.00	2.05
E	1.95	2.00	2.05
e	0.65TYP.		
L	0.23	0.28	0.33
L1	0.60	0.65	0.65
D1	0.90	0.95	1.00
E1	1.10	1.15	1.20
A3	0.152REF		
All Dimensions in mm			

**7. SOLDERING FOOTPRINT**


DFN2020-6S	
Dim	(mm)
X	0.40
X1	0.95
X2	1.70
e	0.65
Y	0.43
Y1	0.75
Y2	1.15
Y3	1.54
Y4	2.39

